

INFORMATION DISCLOSURE CITATION IN AN APPLICATION

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 APPLICANT
QI XIANG

 FILING DATE
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 GROUP
To be assigned

U.S. PATENT DOCUMENTS

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EXAMINER'S INITIALS	CITE NO.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.
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